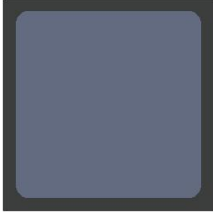


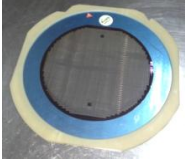





DEVICE TYPE: 45V Trench Sky datasheet

CHIP LAY-OUT	CHIP INFO	DIMENSION / DATA		
 <p>TOP VIEW</p>  <p>SIDE VIEW</p>	V_{RWM}	45V		
	I_{FAV}	3A~30A		
	T_{JMAX}	150°C		
	WAFER SIZE	150 ± 0.3 mm		
	CHIP SIZE	58mil~150mil		
	CHIP THICKNESS	11~12 mils		
	SCRIBE LINE WIDTH	4 mils		
	METALLIZATION			
	- Top Metal			
		Ag	7um	
	Al	7.2um		
- Back Metal				
	Ag	1.7um		
ESD Capability	Minimum Electro-Static Discharge resistance to voltage			
	JEDEC Standard	>8	kv	
	IEC-61000-4-2 Standard	>8		
Delivery	Wafer (6 inch)	Dies with tape	Dies in bottle (≤70mil)	
				

YIELD CUT-OFF: 95%

WAFER MANUFACTURER: Li-ON Microelectronics

LOCATION: Hangzhou, China

Update:2019-11-21



DEVICE TYPE: 45V Trench Sky datasheet

ELECTRICAL RATINGS & CHARACTERISTICS $T_J > 150^\circ\text{C}$ ($T_A = 25^\circ\text{C}$, UNLESS OTHERWISE NOTED)								
SYMBOL	CHIP SIZE (mil)	CONTACT SIZE(mil)	I_{FAV} (A)	Device	RS(A)	IFSM(A)	V_{FMAX}(V)	I_{RMAX}(uA)
Single die	58	48	3	TS8056A	1	80	0.45	50
	72	62	5	TS8083A	1	130	0.45	50
	82	72	10	TS8046A	1	180	0.49	80
	102	94	10	TS6038A	1	275	0.47	50
	110	101	15	TS6042A	1	275	0.5	50
	130	121	25	TS4035A	1	350	0.5	40
	150	142	30	TS4037A	1	350	0.5	45

